



SKYSEMI
思开半导体

SS4406A
30V N-Channel MOSFET

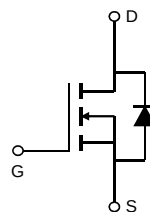
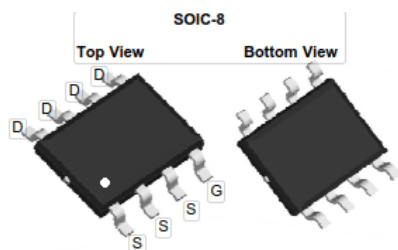
General Description

The SS4406A uses advanced trench technology to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for high side switch in SMPS and general purpose applications.

Product Summary

V_{DS}	30V
I_D (at $V_{GS}=10V$)	13A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 11.5m Ω
$R_{DS(ON)}$ (at $V_{GS} = 4.5V$)	< 15.5m Ω

100% UIS Tested



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	13	A
		10.4	
Pulsed Drain Current ^C	I_{DM}	100	
Avalanche Current ^C	I_{AS}	22	A
Avalanche energy $L=0.5\text{mH}$ ^C	E_{AS}	24	mJ
Power Dissipation ^B	P_D	3.1	W
		2	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	31	40	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^{A D}		59	75	$^\circ\text{C/W}$
Maximum Junction-to-Lead	$R_{\theta JL}$	16	24	$^\circ\text{C/W}$